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Conductance and gating effects at sputtered oxide interfaces

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Cover Page



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Conductance and Gating Effects at Sputtered Oxide Interfaces

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About the cover: The cover shows an illustration of the $\text{LaAlO}_3/\text{SrTiO}_3$ interface. The left side is the LaAlO_3 film and the right side is the SrTiO_3 substrate. The light blue, dark blue, orange, red and gray spheres represent La, Al, Sr, Ti and O atoms, respectively. The light gray squares represent oxygen octahedra.

To my grandfather

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